L Number	Hits	Search Text	DB	Time stamp
-	433	(432/253).CCLS.	USPAT	2004/06/09 07:25
-	332	((432/258) or (432/259)).CCLS.	USPAT	2004/06/09 07:25
-	433	(432/253).CCLS.	USPAT	2004/06/09 07:25
-	259	(((432/258) or (432/259)).CCLS.) not ((432/253).CCLS.)	USPAT	2004/06/09 07:25
-	47	(wafer substrate semiconductor) and ((((432/258) or (432/259)).CCLS.) not ((432/253).CCLS.))	USPAT	2004/06/09 07:36
-	81	(219/443.1).CCLS.	USPAT	2004/06/09 08:16
-	15	(wafer substrate semiconductor) and ((219/443.1).CCLS.)	USPAT	2004/06/09 08:16
-	135	(219/444.1).CCLS.	USPAT	2004/06/09 09:17
-	132	(wafer substrate semiconductor) and ((219/444.1).CCLS.)	USPAT	2004/06/09 10:36
-	126	((wafer substrate semiconductor) and ((219/444.1).CCLS.)) not ((wafer substrate semiconductor) and ((219/443.1).CCLS.))	USPAT	2004/06/09 08:17
-	115	(219/445.1).CCLS.	USPAT	2004/06/09 09:30
-	0	(219/446).CCLS.	USPAT	2004/06/09 09:30
-	46	(219/446.1).CCLS.	USPAT	2004/06/09 09:32
-	0	(219/458).CCLS.	USPAT	2004/06/09 09:32
-	222	(219/458.1).CCLS.	USPAT	2004/06/09 09:32
-	0	(219/458.2).CCLS.	USPAT	2004/06/09 09:32
-	6	(wafer substrate semiconductor) and ((219/458.1).CCLS.)	USPAT	2004/06/09 09:33
-	1365	118/725.ccls. and (wafer substrate semiconductor)	USPAT	2004/06/09 09:33
-	759	(support and (118/725.ccls. and (wafer substrate semiconductor))) not (((432/253).CCLS.) (((432/258) or (432/259)).CCLS.) not ((432/253).CCLS.)) ((219/443.1).CCLS.) ((219/444.1).CCLS.) (((wafer substrate semiconductor) and ((219/444.1).CCLS.)) not ((wafer substrate semiconductor) and ((219/443.1).CCLS.))) ((219/445.1).CCLS.) ((219/446.1).CCLS.))	USPAT	2004/06/09 09:35
-	726	(heat$4 and temperature) and ((support and (118/725.ccls. and (wafer substrate semiconductor))) not (((432/253).CCLS.) (((432/258) or (432/259)).CCLS.) not ((432/253).CCLS.)) ((219/443.1).CCLS.) ((219/444.1).CCLS.) (((wafer substrate semiconductor) and ((219/444.1).CCLS.)) not ((wafer substrate semiconductor) and ((219/443.1).CCLS.))) ((219/445.1).CCLS.) ((219/446.1).CCLS.)))	USPAT	2004/06/09 09:35
-	106	chuck and ((heat$4 and temperature) and ((support and (118/725.ccls. and (wafer substrate semiconductor))) not (((432/253).CCLS.) (((432/258) or (432/259)).CCLS.) not ((432/253).CCLS.)) ((219/443.1).CCLS.) ((219/444.1).CCLS.) (((wafer substrate semiconductor) and ((219/444.1).CCLS.)) not ((wafer substrate semiconductor) and ((219/443.1).CCLS.))) ((219/445.1).CCLS.) ((219/446.1).CCLS.))))	USPAT	2004/06/09 09:57

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-	1	("6409932").PN.	USPAT	2004/06/09 09:57
-	2582	(wafer substrate semiconductor) and "silicon dioxide".ab.	USPAT	2004/06/09 10:29
-	0	("silicon dioxide" with loss) and flourine and ((wafer substrate semiconductor) and "silicon dioxide".ab.)	USPAT	2004/06/09 10:30
-	48	("silicon dioxide" with loss) and ((wafer substrate semiconductor) and "silicon dioxide".ab.)	USPAT	2004/06/09 10:36
-	647	(432/4-6).CCLS.	USPAT	2004/06/09 10:36
-	123	(wafer substrate semiconductor) and ((432/4-6).CCLS.)	USPAT	2004/06/09 10:37
-	68	((wafer substrate semiconductor) and ((432/4-6).CCLS.)) not (((432/253).CCLS.) ((((432/258) or (432/259)).CCLS.) not ((432/253).CCLS.)) ((219/443.1).CCLS.) ((219/444.1).CCLS.) (((wafer substrate semiconductor) and ((219/444.1).CCLS.)) not ((wafer substrate semiconductor) and ((219/443.1).CCLS.))) ((219/445.1).CCLS.) ((219/446.1).CCLS.))	USPAT	2004/06/09 10:51
-	0	"silicon dioxide loss".ti. and (wafer substrate semiconductor)	USPAT	2004/06/09 10:51
-	0	"silicon dioxide loss".ab. and (wafer substrate semiconductor)	USPAT	2004/06/09 11:02

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